

# Accepted Manuscript

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PII: S2352-2143(18)30141-2

DOI: [10.1016/j.cocom.2018.e00304](https://doi.org/10.1016/j.cocom.2018.e00304)

Article Number: e00304

Reference: COCOM 304

To appear in: *Computational Condensed Matter*

Received Date: 4 May 2018

Revised Date: 15 May 2018

Accepted Date: 17 May 2018

Please cite this article as: F.Z. Chafi, E. Salmani, L. Bahmad, N. Hassanain, F. Boubker, A. Mzerd, First principle calculations with SIC correction of Fe-doped CuO compound, *Computational Condensed Matter* (2018), doi: 10.1016/j.cocom.2018.e00304.

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# First principle calculations with SIC correction of Fe-doped CuO compound

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## ABSTRACT

In this work, the electronic properties of Fe-doped CuO ( $\text{Cu}_{1-x}\text{Fe}_x\text{O}$ ) thin films are studied by using a standard density functional theory (DFT). This approach is based on the ab-initio calculations under the Korringa-Kohn-Rostoker coherent potential approximation (KKR-CPA). We carried out our investigations in the framework of the general gradient approximation (GGA) and self-interaction-corrected (SIC). The density-of-states (DOSs) in the energy diagrams are presented and discussed. The computed electronic properties of the studied compound ( $\text{Cu}_{1-x}\text{Fe}_x\text{O}$ ) confirm the half-metallicity nature of this material. In addition, the absorption spectra of the studied compound within the Generalized Gradient Approximation GGA, as proposed by Perdew–Burke–Ernzerhof (PBE) and GGA-PBE -SIC approximations are examined. When compared with the pure CuO, the Fermi-levels of doped structures ( $\text{Cu}_{1-x}\text{Fe}_x\text{O}$ ) are found to move to the higher energy directions. To complete this study, the effect of Fe-doping method in CuO has transformed the material to half-metallic one. We found a high wide impurity band in two cases of approximations LDA and SIC methods.

**Keywords:** Ab-initio calculation; Fe-doped CuO; KKR-CPA; GGA; SIC correction; Half-metallicity.

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